

International Conference

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2. M. M. Shahidul Hassan and Omiya Hassan, "The Importance of Changing the Traditional Mode of Higher Education in Bangladesh: Creating Huge Job Opportunities for Home and Abroad", ICEEE 2019 Vienna, Austria, 20-22 June 2019
<http://internationalresearchconference.org/conference/2019/06/vienna/ICEEE>
3. M. M. Shahidul Hassan, "National framework for engineering education delivery models in South Asia," International Conference on Education Social Sciences and Humanities (SOCIO-INT15), Istanbul, Turkey, 8-10 July 2015.

4. M M Shahidul Hassan,,”Challenges and Opportunities for Engineering Education in Bangladesh,” IEOM Symposium on Global Engineering Education, December 19, 2015, Dhaka, Bangladesh..
5. M. M. Shahidul Hassan, “Outcome Based Engineering Education: A paradigm shift.” ICECE 2012 Conference, Dhaka, Bangladesh.
6. M. M. Shahidul Hassan, “Implementing Outcome Based Engineering Education in Bangladesh,” Advanced Education and Management [ICAEM2014], Jan 04 –Jan 06 2014, Beijing, China.